

WS7804Q

0.1GHz - 3GHz SP4T Antenna Switch

Descriptions

The WS7804Q is a Single Pole, Four-Throw (SP4T) switch, consisting of an SP4T switch that has 4 identical paths, and a GPIO controller. The device is optimized for GSM/EDGE, WCDMA, TD-SCDMA and LTE systems and can be used up to 3GHz applications. The low current consumption makes this device very suitable for battery operated applications. The WS7804Q is manufactured in a compact 2.0mm x 2.0 mm, 14-pin QFN package.

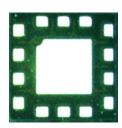
Features

- Small, low profile package 2.0mm x 2.0mm x 0.55mm
- Working frequency up to 3GHz
- Very low insertion loss
- Excellent isolation performance
- Low power consumption
- Exceptional linearity performance for 3G/4G application
- Low harmonic generation
- Very good ESD performance

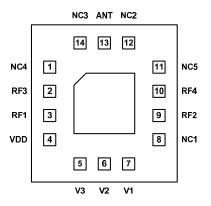
Applications

- Cell phones
- Tablets
- Other RF front-end modules

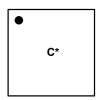
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QFN 2X2-14L (Bottom view)



Pin configuration (Top view)



C = Device code

* = Month code (A~Z)

Marking(Top view)

Order information

Device	Package	Shipping		
WS7804Q-14/TR	QFN2X2-14L	3000/Reel&Tape		

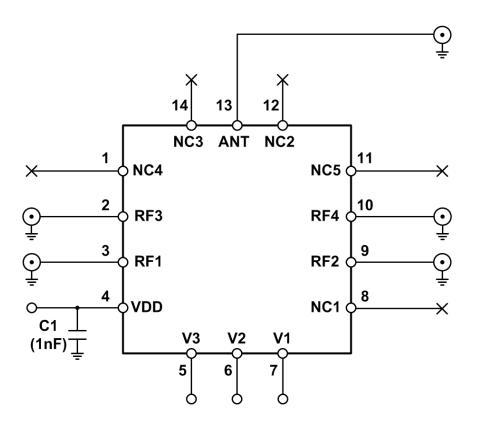


Pinning information

Pin	Function	Description	Transparent top view						
1	N/C	Not connected							
2	RF3	RF I/O path 3			NC3	ANT	NC2		
3	RF1	RF I/O path 1							
4	VDD	DC power supply			14	13	12		
5	V3	DC control voltage3	NC4	1				11	NC5
6	V2	DC control voltage2							
7	V1	DC control voltage1	RF3	2				10	RF4
8	N/C	Not connected	RF1	3				9	RF2
9	RF2	RF I/O path 2							
10	RF4	RF I/O path 4	VDD	4				8	NC1
11	N/C	Not connected			5	6	7		
12	N/C	Not connected					<u> </u>		
13	ANT	Antenna port			V3	V2	V1		
14	N/C	Not connected							

Note: Bottom ground paddles must be connected to ground.

Application information



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Recommended operating conditions

Parameters	Conditions	Specifications			Unit
		Min.	Тур.	Max.	
ESD Rating					
ESD All Pins	HBM, JESD22-A114			1000	V
Power Supply					
Power Supply Voltage	Operating Voltage	2.4	2.8	3.0	V
Power Supply Current	V _{DD} ≤3.0V	20	28	70	μA
Shutdown Mode Supply Current	V1/2/3=1.8V, VDD=3V		7		μA
Control Voltage					
Logic Control "Low"		0	0	0.3	V
Logic Control "High"		1.2	1.8	2.7	V
RF Impedance					
RF Port Input and Output Impedance			50		Ω

Absolute maximum ratings

Maximum ratings are absolute ratings, exceeding only one of these values may cause irreversible damage to the integrated circuit.

Items	Value	Unit	
VDD Voltage	-0.3 to +3.0	V	
Control Voltage	-0.3 to +2.7	V	
Maximum Input Power @ RF ports	31@0.7GHz, 33@2.7GHz	dBm	
Operation Temperature	-40 to +85	°C	
Storage Temperature	-65 to +150	°C	

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Characteristics (RF spec)

Nominal test condition unless otherwise stated. All unused ports are 50Ω terminated. VDD = 2.8V, Temp = +25°C. P_{IN} =0dBm.

Parameters	Conditions	Specifications			Unit
		Min.	Тур.	Max.	
Insertion Loss	0.1GHz to 1.0GHz		0.45	0.60	
(RF1/RF2/RF3/RF4)	1.0GHz to 2.0GHz		0.55	0.70	dB
(RF1/RF2/RF3/RF4)	2.0GHz to 2.7GHz		0.75	0.90	
loclotion	0.1GHz to 1.0GHz	30			
Isolation (ANT to RF1/RF2/RF3/RF4)	1.0GHz to 2.0GHz	25			dB
	2.0GHz to 2.7GHz	18			
Return Loss	0.1GHz to 1.0GHz	20			
. 1010 2000	1.0GHz to 2.0GHz	15			dB
(ANT/RF1/RF2/RF3/RF4)	2.0GHz to 2.7GHz	15			
Second Harmonics	P _{IN} =+26dBm@0.88G		84		dBc
(RF1/RF2/RF3/RF4)	1 N=1200Bin@0.00G		04		abc
Third Harmonics	P _{IN} =+26dBm@0.88G		87		dBc
(RF1/RF2/RF3/RF4)	1 N=1200Bin@0.00G		07		ubc
0.1dB Compression Point	@0.7GHz		30		dBm
(RF1/RF2/RF3/RF4)	@2.7GHz		32		ubiii
3 rd Order Input Intercept Point	P ₂ = +20dBm,				
(RF1/RF2/RF3/RF4)	P_1 = -15dBm,		63		dBm
(IXI I/IXI Z/IXE 3/IXE4)	Note 1				

Note 1: f_2 =836.5MHz, f_1 =791.5MHz, f_{IMD3} =881.5MHz

Truth Table for Operation

SP4T Mode	V1	V2	V3
RF1	0	0	0
RF2	0	0	1
RF3	0	1	0
RF4	0	1	1
Shutdown	1	1	1

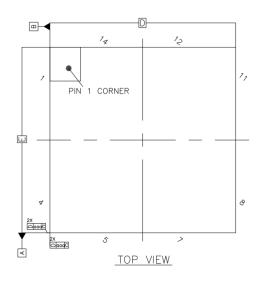
Note: Any state other than that described in this Table places the switch into an undefined state. An undefined state will not damage the device.

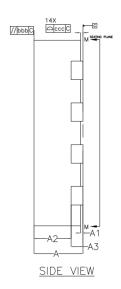
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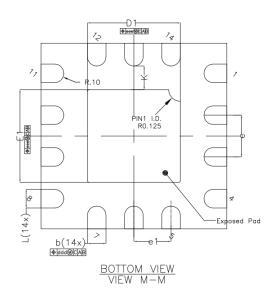


Package outline dimensions

QFN 2X2-14L



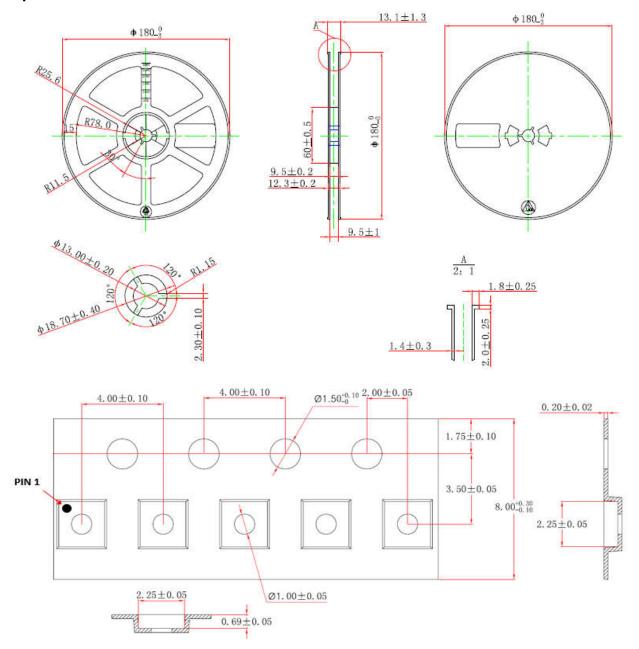




			MILLIMETER			
DESCRIPTION		SYMBOL	MIN	NOM	MAX	
TOTAL THICKNESS		Α	0.477	0.527	0.577	
STAND OFF		A1	0.00	0.02	0.05	
MOLD THICKNESS		A2	0.35	0.40	0.45	
L/F THICKNESS		A3	0.127 REF			
LEAD WIDTH		ь	0.15	0.20	0.25	
DODY 0175	X	D	1.95	2.00	2.05	
BODY SIZE	Υ	E	1.95	2.00	2.05	
LEAD PITCH		е	0.45 BSC			
LEAD PITCH		e1	0.40 BSC			
LEAD LENGTH		L	0.195	0.245	0.295	
EP SIZE	X	D1	0.95	1.00	1.05	
EF SIZE	Υ	E1	0.95	1.00	1.05	
LEAD TO PAD SPACE		К	0.205	0.255	0.305	
	Toleran	ce of form	and positio	n		
PACKAGE EDGE TOLERANCE		aaa	0.1			
MOLD FLATNESS		bbb	0.1			
LEAD COPLANARITY		ccc	0.08			
LEAD POSITION OFFSET		ddd	0.1			
EXPOSED PAD OFFSET		eee	0.1			



Tape and Reel Information



Note:

- 1. CARRIER TAPE COLOR IS BLACK.
- 2. COVER TAPE WIDTH: 9.50±0.1.
- 3. COVER TAPE COLOR IS WHITE.
- 4. ESD-SURFACE RESISTIVITY MEET EIA/JEDEC TNR SPECIFICATION.
- 5. ALL DIMENSIONS ARE IN MILLIMETER.

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